Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Very fast switching
- Enhanced power dissipation capability: P_{tot} = 890 mW
- ElectroStatic Discharge (ESD) protection 2 kV HBM

3. Applications

- · Relay driver
- High speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------|----------------------------------|---|-----|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| V_{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$ | [1] | - | - | -3.3 | Α |
| Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 25 °C | | - | 67 | 78 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | G | gate | <u></u> 3 | D I |
| 2 | S | source | | |
| 3 | D | drain | 1 | G S 017aaa259 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|----------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PMV65XPE | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| PMV65XPE | %KE |

[1] % = placeholder for manufacturing site code

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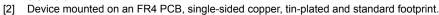
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | V |
| V _{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$ | [1] | - | -3.3 | Α |
| | | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | -2.8 | Α |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -1.8 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs | | - | -12 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 480 | mW |
| | | | [1] | - | 890 | mW |
| | | T _{sp} = 25 °C | | - | 6250 | mW |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain o | liode | | | | | |
| Is | source current | T _{amb} = 25 °C | [1] | - | -0.9 | Α |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



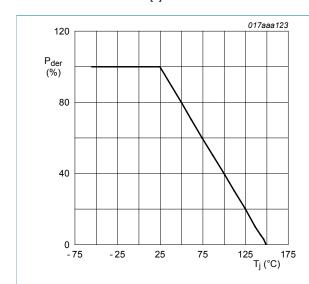


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

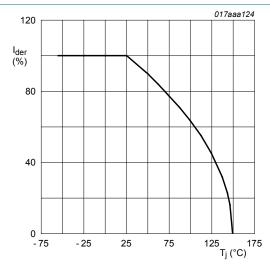


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

PMV65XPE

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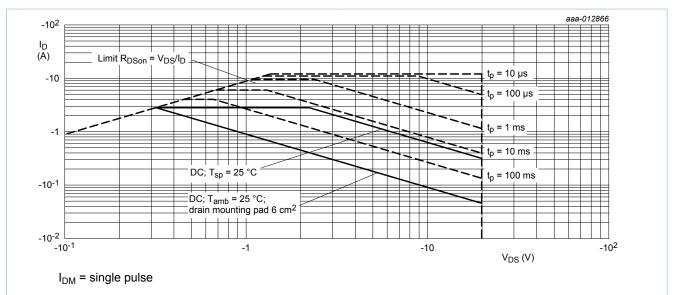


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance | _ | [1] | - | 230 | 260 | K/W |
| | from junction to ambient | | [2] | - | 120 | 140 | K/W |
| | ambient | in free air; t ≤ 5 s | [2] | - | 85 | 100 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 15 | 20 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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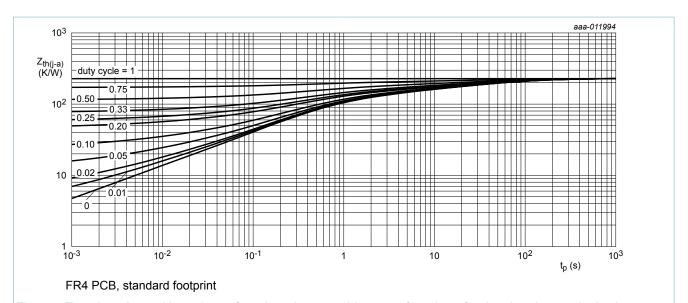


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

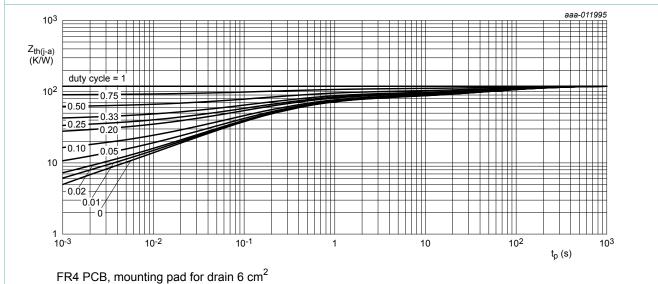


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--------------------------------|--|-------|-------|-------|------|
| Static char | acteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | -20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C | -0.75 | -1 | -1.25 | V |
| I _{DSS} | drain leakage current | V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C | - | - | -1 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μΑ |
| | | V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μΑ |
| | | V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 2 | μΑ |
| | | V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -2 | μΑ |
| R _{DSon} | drain-source on-state | V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 25 °C | - | 67 | 78 | mΩ |
| | resistance | V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 150 °C | - | 98 | 114 | mΩ |
| | | V_{GS} = -2.5 V; I_D = -2.2 A; T_j = 25 °C | - | 99 | 125 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = -10 V; I_{D} = -2 A; T_{j} = 25 °C | - | 7.4 | - | S |
| R _G | gate resistance | f = 1 MHz | - | 11.6 | - | Ω |
| Dynamic c | haracteristics | | | | | , |
| Q _{G(tot)} | total gate charge | V_{DS} = -10 V; I_{D} = -2.8 A; V_{GS} = -4.5 V; | - | 5 | 9 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 1.1 | - | nC |
| Q_{GD} | gate-drain charge | | - | 1.1 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$ | - | 618 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 80 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 58 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -10 V; I_{D} = -2.8 A; V_{GS} = -4.5 V; | - | 7 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$ | - | 19 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 36 | - | ns |
| t _f | fall time | | - | 17 | - | ns |
| Source-dra | in diode | | l . | | 1 | 1 |
| V_{SD} | source-drain voltage | $I_S = -0.85 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | -0.75 | -1.2 | V |

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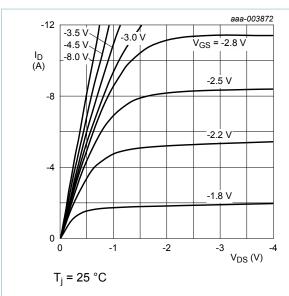
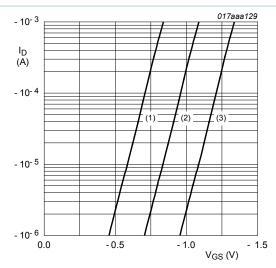


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i$$
 = 25 °C; V_{DS} = -3 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

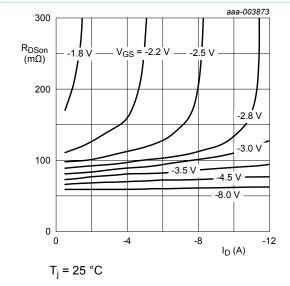


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

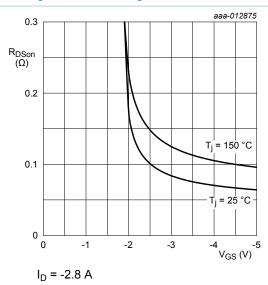


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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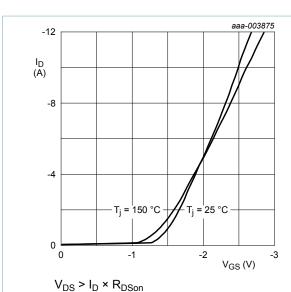


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

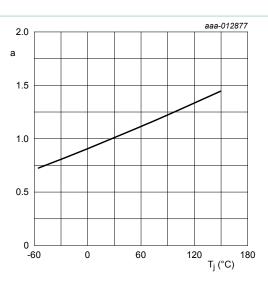


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

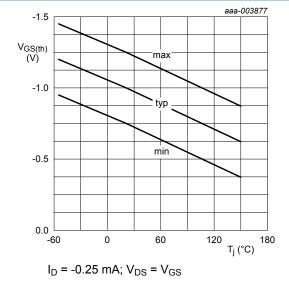
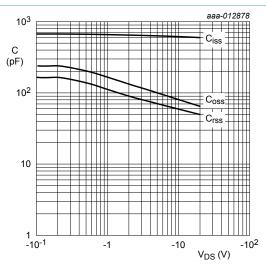


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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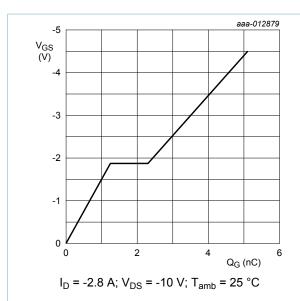


Fig. 14. Gate-source voltage as a function of gate charge; typical values

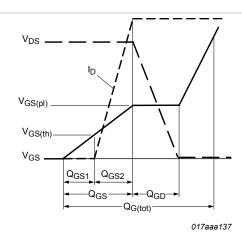


Fig. 15. MOSFET transistor: Gate charge waveform definitions

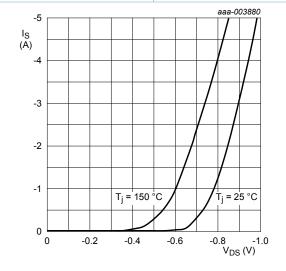
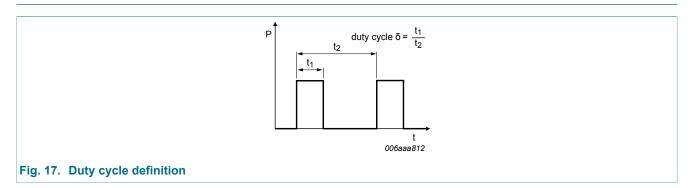


Fig. 16. Source current as a function of source-drain voltage; typical values

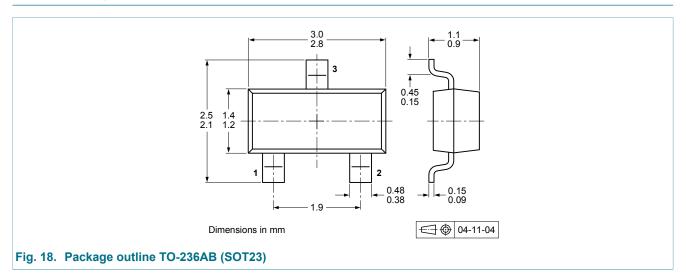
 $V_{GS} = 0 V$

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11. Test information

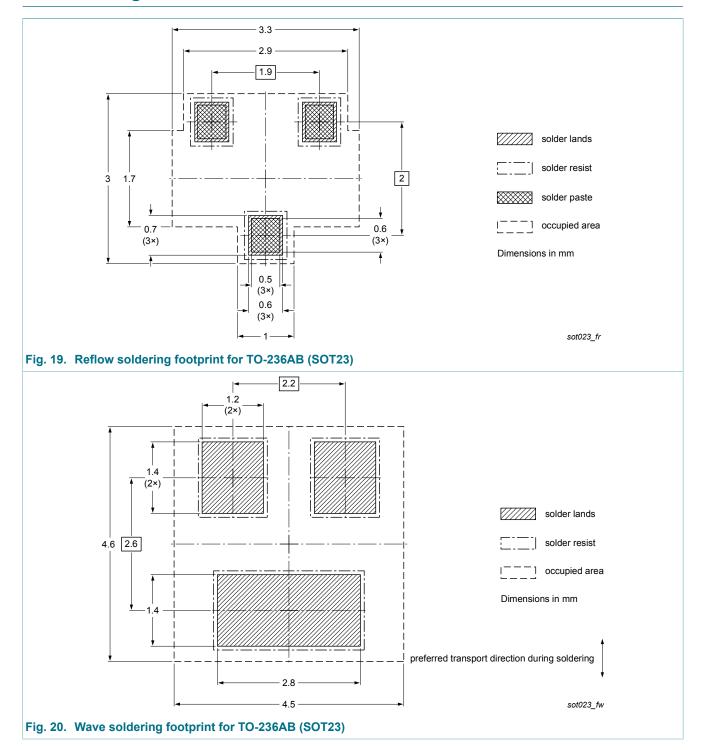


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMV65XPE v.1 | 20140425 | Product data sheet | - | - |

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|--------------------------------------|--------------------|---|
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